

Photoemission (I) Spectroscopy

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Outline

- 1. What is photoemission spectroscopy?
- 2. Fundamental aspects of photoemission.
- 3. Examples.
- 4. Increase bulk sensitivity: HAXPES.
- 5. Challenging future directions.

General reference books:

- 1. "Photoelectron Spectroscopy" 3rd Ed. by S. Hufner, Springer-Verlag 2003
- 2. "Angle-Resolved Photoemission: Theory and Current Applications", S. D. Kevan, ed., Amsterdam; Elsevier 1992

What is photoemission?



Photon in -> electron out (emission)

What are the samples and probed states?

Atoms Molecules Nanoprticles Solids atomic orbitals (states) molecular orbitals core level states (atomic like) valence bands/states core level states (atomic like) valence bands core level states (atomic like)

What is photoemission spectroscopy? (photoelectron spectroscopy) (PES)



Initial state: ground (neutral) state

Conservation of energy

 $E_k = hv + E_i - E_f$ (most general expression)

 E_k : photoelectron kinetic energy $E_i(N)$: total initial state system energy $E_f(N-1)$: total final state system energy Electron energy analyzer



Final state: hole (excited) state



Energy Distribution Curve (EDC) (Spectrum)

Single particle description of energy levels (Density of States) (most convenient in PE)



Energetics in PES



Hufner, Damascelli

 $E_{k} = hv - E_{B} - \phi$

 E_v : vacuum (energy) level E_F : Fermi (energy) level $\phi = E_v - E_F$: work function E_0 : bottom of valence band $V_0 = E_v - E_0$: inner potential

Conservation of energy

 E_k^{max} marks E_F in spectra E_B measured relative to $E_F = 0$

Usually fixed photon energy scanning not needed

An XPS Energy Distribution Curve (EDC)



Hufner

Light sources and terminology

Ultraviolet Photoemission Spectroscopy (UPS) UV He lamp (21.2 eV, 40.8 eV) valence band PE, direct electronic state info

X-ray Photoemission Spectroscopy (XPS) (Electron Spectroscopy for Chemical Analysis) (ESCA) x-ray gun (Al: 1486.6 eV, Mg: 1253.6 eV) core level PE, indirect electronic state info chemical analysis

Synchrotron radiation:

continuous tunable wavelength valence band: <100 eV, maybe up to several keV core level: 80-1000 eV, maybe up to several keV depending on core level binding energies

Inelastic Electron Mean Free Path (IMFP)

 $I(d) = I_o e^{-d/\lambda(E)}$

 $\lambda(E)$: IMFP depending on kinetic energy relative to E_{r}



Fig.1.9. Electron escape depth as a function of their kinetic energy for various metals. The data indicate a universal curve with a minimum of $2\div 5$ Å for kinetic energies of $50\div 100$ eV. The scatter of the data is evident from the values obtained at $E_{kin} = 1480$ Hufner eV

Minimum due to electron-electron scattering, mainly plasmons

PE is a surface sensitive technique! (requires UHV) High energy photoemission: several keV to increase bulk sensitivity

Element	K 1s	L ₁ 2s	L ₂ 2p _{1/2}	L ₃ 2p _{3/2}	M ₁ 3s	M ₂ 3p _{1/2}	M3 3p3/2	M ₄ 3d _{3/2}	M5 3d5/2	N ₁ 4s	N ₂ 4p _{1/2}	N ₃ 4p _{3/2}	
1 H	13.6							•					
2 He	24.6*								\sim			and the second	
3 Li	54.7*								())	٦re	Ie\	iel hinding energies al	P
4 Be	111.5*											or binding chorgics a	
5 B	188*											and the second	•
6 C	284.2*								<u> </u>	nara	acte	eristic of each orbital c)T
7 N	409.9*	37.3*											
8 O	543.1*	41.6*							_				
9 F	696.7*								ea	acn	ele	ement	
10 Ne	870.2*	48.5*	21.7*	21.6*									
11 Na	1070.8†	63.5†	30.65	30.81									
12 Mg	1303.0†	88.7	49.78	49.50									
13 Al	1559.6	117.8	72.95	72.55									
14 Si	1839	149.7*b	99.82	99.42						$\sim \sim \sim$		rinto	
15 P	2145.5	189*	136*	135*					- E I	nut	a it	Innis	
16 S	2472	230.9	163.6*	162.5*						3			
19 4-	2822.4	270*	202*	200*	20.2*	15.0*	15.7*						
10 Ar	2608.4*	279.5*	207.2*	246.4*	29.5*	19.9*	19.7*						
19 K 20 Ca	4038.5*	576.0° 428.44	297.5*	294.0*	54.0°	25.4+	25.44						
20 Ca	4038.5	430.41	549.71	540.21	44.5	25.4	23.4		\mathbf{C}	n ro		al RE independent of	
23 V	5465	626.7†	519.8†	512.1†	66.3†	37.2*	37.2*			JE	IEV		
24 Cr	5989	696.0†	583.8†	574.1*	74.1*	42.2*	42.2†					•	
25 Mn	6539	769.17	649.9† 710.0†	638.7 1	82.37	47.2*	47.27		nh	not/	nn a	anaravusad	
26 Fe	7112	844.67	719.9	706.87	91.37	52.74	52.77		μ	IUU		Energy used	
27 Co	2222	925.17 1008.64	793.2T	/ /8.17	110.84	58.9Y	59.97 66.24					07	
28 INI 20 Cu	8070	1006.01	052.24	022.71	102.54	77.24	75.14						
29 Cu 20 Zn	0650	1106.71	952.51	952.7	122.51	01.4*	73.1 88.6*	10.2*	10.1*				
30 Zli 31 Ga	10367	1200.0*b	1143.2+	1116.4+	159.8*	102.5*	100.0+	18.7*	18.74				
32 Ge	11103	1299.0 0 1414 6*h	1248 1*b	1217.0*h	180.1*	124.0*	120.8*	29.8	20.2				
33 As	11867	1527.0*b	1359.1*b	1323.6*b	204.7*	146.2*	141.2*	41.7*	41.7*				
34 Se	12658	1652.0*b	1474.3*b	1433.9*b	229.6*	166.5*	160.7*	55.5*	54.6*				
35 Br	13474	1782*	1596*	1550*	257*	189*	182*	70*	69*				
36 Kr	14326	1921	1730.9*	1678.4*	292.8*	222.2*	214.4	95.0*	93.8*	27.5*	14.1*	14.1*	
37 Rb	15200	2065	1864	1804	326.7*	248.7*	239.1*	113.0*	112*	30.5*	16.3*	15.3 *	
38 Sr	16105	2216	2007	1940	358.7†	280.3*	270.0†	136.0*	134.2†	38.9*	21.3	20.1†	
39 Y	17038	2373	2156	2080	392.0*b	310.6*	298.8*	157.7†	155.8†	43.8*	24.4*	23.1*	
40 Zr	17998	2532	2307	2223	430.3†	343.5†	329.8†	181.1*	178.8†	50.6†	28.5*	27.1†	
41 Nb	18986	2698	2465	2371	466.6†	376.1†	360.6†	205.0*	202.3†	56.4†	32.6†	30.8†	
42 Mo	20000	2866	2625	2520	506.3†	411.6†	394.0†	231.1†	227.9†	63.2*	37.6†	35.5†	
43 Tc	21044	3043	2793	2677	544*	447.6	417.7	257.6	253.9*	69.5*	42.3*	39.9*	
44 Ru	22117	3224	2967	2838	586.1*	483.5†	461.4†	284.2†	280.0^{+}	75.0†	46.3†	43.2†	
45 Rh	23220	3412	3146	3004	628.1†	521.3†	496.5†	311.9*	307.2*	81.4*b	50.5†	47.3†	
46 Pd	24350	3604	3330	3173	671.6†	559.9†	532.3†	340.5†	335.2†	87.1*b	55.7†a	50.9†	
47 Ag	25514	3806	3524	3351	719.0†	603.8*	573.0*	374.0*	368.3	97.0*	63.7†	58.3†	

Table 1-1. Electron binding energies, in electron volts, for the elements in their natural forms.

Core level photoemission: chemical analysis of elements





Surface core level shift (chemical and/or environmental)

A case study of IMFP applied to PE of CdSe nano particles with tunable SR How to choose photon energies for valence and different core levels with the max surface sensitivity?

Actual choices:

Cd 3d _{5/2} :	480 eV
Se 3d:	120 eV
Valence band:	50 eV

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 $E_k \sim 45-74 \text{ eV}$, most surface sensitive

Wu, PRB 2007 NSRRC

Core level photoemission: chemical shift

higher oxidation state => higher BE





higher emission angle
→ more surface sensitive
(IMFP) Pi, SS 2001 NSRRC

Auger Electron Spectroscopy

Core electron ionized by photons or high energy electrons Non-radiative core hole decay → Auger electron emission Radiative decay

 \rightarrow Fluorescent x-ray emission

(a) Photoelectric absorption







(c) Auger electron emission



Comparison between PES and AES PES: constant BE, Ek shift with changing photon energy AES: constant Ek, apparent BE shift with changing photon energy (synchrotron)

Photoemission Process



Conceptually intuitive, Simple calculation works

Rigorous, requires sophisticated calculation

Schematic wave functions of initial and final states (valence band initial states)



(c) Bulk Bloch state

(f) Bulk Bloch final state

Electron kinetic energy inside and outside of solids

Inner potential: $E_V - E_0$



Concept of inner potential is used to deduce 3D band structure from PE data assuming free electron like final state inside solids

Angle Resolved Photoemission Spectroscopy (ARPES)



Electron emission angle: Θ Photon incident angle: ϕ , *s*- and *p*-polarization

Conservation of linear momentum parallel to the surface



 k_{\perp} (inside) $\neq k_{\perp}$ (outside) because of inner potential

Ultimately to deduce band dispersion $E(k_{\perp})$ or $E(k_{\perp}, k_{\parallel})$

Normal emission: $\theta = 0$, or $k_{\parallel} = 0$, most used detection geometry

Band Mapping (3D) $E(k_{\perp}, k_{\parallel}=0)$



Vertical transition (using visible, uv and soft x-rays) at normal emission

For hard x-ray photon momentum cannot be neglected

Using different hv at normal emission to map out $E(k_{\perp})$

Bulk band structure and Fermi surfaces

Fermi surfaces:

Electron pockets and hole pockets Related to Hall coefficient Electric conductivity Magnetic susceptibility

(nearly free electron like) sp-band

Small dispersion *d*-band more localized state

Large dispersion *sp*-band extended state

Dispersion of a band can tell how localized or extended a state is in a solid



Fig. 10-15 Various aspects of the Fermi surface of Cu. (a) The Brillouin zone of an fcc lattice with some special points labeled. (b) A (110) section of the Brillouin zone. See the text for the meaning of the internal curves. (c) The proposed Fermi surface of Cu. (d) The extended zone picture of a (110) section of the Fermi surface showing the dog bone orbits.

Gap below $E_F(=0)$ at L-point





Hufner

 $() \longrightarrow (001)$

Quantum well states: manifestation of particle in a box in real materials



Ag(111) thin films expitaxially grown on Au(111) substrate



Quantized discretely along z-direction Energy levels depend on film thickness *L*

Nearly free electron like in xy-plane

Bulk projected bands along ΓL of Au and Ag, respectively





Anneal to 180 K QWS appear minimal flat dispersion Small localized domains within xy-plane

Anneal to 189 K Coexistence of two kinds of dispersion

Anneal to 258 K Well developed dispersion Large, good crystalline domains in xy-plane



Same QWS energies → Same crystalline film thickness along z even though lateral crystalline domains grow from small to large



Proposed growth model

Annealing Temp ——

One-particle spectral function near E_F measured by ARPES with many-particle correction (quasi-particle)

$$A(k,\omega) = -\frac{1}{\pi} \frac{\Sigma''(k,\omega)}{\left[\omega - \varepsilon_k - \Sigma'(k,\omega)\right]^2 + \left[\Sigma''(k,\omega)\right]^2}$$

 ε_k : single particle energy without many-particle correction $\omega = 0$: E_F

Self energy correction due to interaction with phonons, plasmons and electrons, etc.

 $\Sigma(k,\omega) = \Sigma'(k,\omega) + i\Sigma''(k,\omega)$

Real part: shift observed peak energy from single particle energy Imaginary part: peak FWHM = 2 Σ "

Many-Body Effects in Angle-Resolved Photoemission: Quasiparticle Energy and Lifetime of a Mo(110) Surface State

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In a high-resolution photoemission study of a Mo(110) surface state various contributions to the measured width and energy of the quasiparticle peak are investigated. Electron-phonon coupling, electron-electron interactions, and scattering from defects are all identified mechanisms responsible for the finite lifetime of a valence photohole. The electron-phonon induced mass enhancement and rapid change of the photohole lifetime near the Fermi level are observed for the first time.



Photoemission cross section in single particle approximation (1st step in 3-step model, inside bulk)

$$\frac{d\sigma}{d\Omega} \propto \sum \left| \left\langle \Psi_f \left| A \cdot p \right| \Psi_i \right\rangle \right|^2 \cdot \delta \left(E_f - E_i - h\nu \right) \\ M_{fi} = \left\langle \Psi_f \left| A(r) \cdot p \right| \Psi_i \right\rangle \cong A(0) \cdot \left\langle \Psi_f \left| p \right| \Psi_i \right\rangle \propto A(0) \cdot \left\langle \Psi_f \left| r \right| \Psi_i \right\rangle$$

dipole approximation

- A : polarization vector
- Ψ_i : initial state (orbital) wave function (1s, 2p, valence states etc.) contain orbital symmetry information

 Ψ_f : final state (orbital) wave function ~ exp(*ik r*) for high kinetic energy photoelectrons, no orbital symmetry retains (non-resonance photoemission) (orbital symmetry in final state is important in near edge absorption measurements (XAS) and in intermediate state in resonance photoemission) Dipole transition rule: $\Delta l = \pm 1$

Symmetry selection rule for initial (valence) state governed by matrix element e.g. suppose A(0) = Ax, $\langle e^{ikz} | x | \psi_i(x) \rangle = 0$ if $\psi_i(-x) = +\psi_i(x)$ *Important for crystalline samples*

Symmetry of states in ARPES determined by selection rule example: LiCu2O2



Cu²⁺O²⁻₂ chains along b-axis built by edge sharing Cu²⁺O²⁻₄ plaquettes

 $Cu^{2+}: 3d^9 \rightarrow spin-1/2$

Quasi-1D spin-1/2 chain

Coexistence of spin-spiral long range order with ferroelectricity \rightarrow multiferronic

Ideal spin-1/2 1D chain system will have spin-charge separation of photo-hole decay Does it happen on LiCu2O2? Must be checked by ARPES (not discussed further)

Will focus on symmetry of states determined by ARPES with polarization



Basic building unit: CuO4 planar plaquette

Highest energy state: Cu 3dxy and O 2p antibonding (AB) state

Still keeps dxy symmetry



Normal emission $|f\rangle = \exp(ikz)$ even to all symmetry op [i> even to y'z-plane, Ax' odd to y'z-plane <f| Ax' |i> = <+| - | +> = 0, forbidden

Off-normal emission [f> = exp(ikz+kx') even to x'z-plane |i> even to x'z-plane, Ax' even to x'z-plane <f| Ax' |i> = <+| + | +> != 0, allowed



Normal emission [f> = exp(ikz) even to all symmetry op [i> odd to xz-plane, Ax even to xz-plane <f| Ax |i> = <+| + |-> = 0, forbidden

Off-normal emission $|f\rangle = \exp(ikz+ikx)$ even to xz-plane |i> odd to xz-plane, Ax even to xz-plane <f| Ax |i> = <+| + |-> = 0, forbidden

Focus on B.E. = 0.7 eV peak at Y'



The highest energy peak at 0.7 eV has dxy symmetry!

ARPES for valence band PE uses primarily VUV light because

- 1. Better absolute photon energy resolution for most BLs designed as const $\Delta E/E$.
- 2. Better photoionization cross section at low photon energy.
- 3. Better momentum resolution for a given angular resolution. $\Delta k = 0.5123 \sqrt{(Ek)} \cos(\theta) \Delta \theta$

SX ARPES has been tried for increasing bulk sensitivity, more free electron like final states and reduced matrix element effects. The increasing bulk sensitivity will be discussed.

NSRRC U9 BL21B1 BL and high resolution photoemission end station



Hemispherical electron energy analyzer



R1 : radius of inner sphere R2 : radius of outer sphere Ro=(R1+R2)/2 : mean radius and along electron path V1: inner potential V2: outer potential Ep: pass energy = electron kinetic energy along mean radius

Resonance photoemission (near-edge absorption followed by Auger like electron emission)

e.g. Ce³⁺ (4f¹) Intensity enhanced by absorption Predominantly 4f DOS 4f mixed with other DOS e. e intermediate state 4f 4f 4f E_F E_F 4f 4f 4f Auger like Absorption + emission 3d/4d 3d/4d 3d/4d **Resonance PE Direct PE**

Comments on photoelectron IMFP

Valence band PE using VUV and SX has IMFP near minimum, very surface sensitive. It is great to probe surface electronic structure such as surface states and surface resonances.

Many strongly correlated systems have electronic structure sensitive to coordination, thus surface contains different electronic structure from that of deeper bulk. Great surface sensitivity posts a serious problem to probe true bulk properties.

Need larger IMFP by using higher energy photons to enhance bulk sensitivity.

letters to nature

2000

Probing bulk states of correlated electron systems by high-resolution resonance photoemission

A. Sekiyama*, T. Iwasaki*, K. Matsuda*, Y. Saitoh†, Y. Ônuki‡ & S. Suga*



By using Ce 3d \rightarrow 4f Res. PE near 880 eV surface 4f component becomes greatly reduced compared to 4d \rightarrow 4f Res. PE near 120 eV, the resulting spectra are closer to true bulk 4f DOS.

Drive to go to even higher photon energies into hard x-ray regime

HArd X-ray PhotoEmission Spectroscopy (HAXPES)

HAXPES not only reach even closer to true bulk properties of strongly correlated systems, but also becomes capable of probing interface electronic structure, Very difficult using conventional VUV/SX.

HAXPES example: Hard x-ray photoemission on Si-high k insulator buried interface



 $hv = 6 \text{ keV}, \Delta E \sim 0.24 \text{ eV}$ Take-off angle dependence => non-destructive depth profile Can probe buried interface at 35 nm ! (achievable only by hard x-ray PE)

NSRRC HAXPES project at SPring-8

Why Hard X-rays? Electron IMFP (probing depth) and Cross section



Higher Ek for deeper probing depth or more bulk sensitivity, for strongly correlated systems and interface properties Photoemission signal (σ · λ) decreases rapidly > 1 keV Need photon source of higher flux/brightness (modern SR), efficient BL design and good electron analyzers HAXPES is a low count rate, photon hungry experiment!

Optical design concept





Layout of the side beamline of BL12XU



Diamond monochromator: installed Aug. 3, 2007

Commission of SPring-8 BL12XU SL HAXPES end station

MBS energy analyzer End station



In collaboration with Cologne U of Germany 2x10⁵ 8020 8025 8030 8035 8040 8045 Kinetic energy (eV) Low resolution w/o HRM 8 keV



Si(333) HRM, 7.6 keV

Challenging future directions of Photoemission Spectroscopy

 ARPES at submicron to tens of nanometer scale, using Schwatzchild optics or zone plates. Need brighter light sources.

2. Time-resolved PES.

Pump-probe: dynamics. Need efficient detection and brighter sources. lasers or laser+SR.

Thanks for your attention